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AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of claims:

- 1. (Currently Amended) A thin film transistor, comprising:
- a stepped substrate provided with a sidewall between upper and lower portions thereof;

an active layer formed on the stepped substrate;

a gate insulation film formed on a lower portion of the active layer and a sidewall <u>portion</u> of the active layer contiguous the lower portion of the active layer and <u>the</u> sidewall of the stepped substrate, respectively;

an insulating film formed on a lower portion of the gate insulation film and a sidewall <u>portion</u> of the gate insulating film contiguous the lower portion of the gate insulating film and <u>the</u> sidewall <u>portion</u> of the <u>stepped substrate</u> <u>active layers</u>, respectively;

a gate electrode formed on the gate insulation film corresponding to an upper part of the sidewalls of the substrate and the insulation film;

impurity regions in the active layer corresponding to the upper and lower portions of the substrate; and

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an offset region formed on the whole a lower region of the oidewall and cubstrate corresponding to the insulating film as a single region sidewall portion of the active layer and the lower portion of the active layer below a bottom of the insulating layer.

2. (Original) The thin film transistor of claim 1, wherein the stepped substrate is formed on an insulating material.

3. (CANCELLED)

- 4. (Original) The thin film transistor of claim 1, wherein the active layer is a semiconductor film.
- 5. (Currently Amended) The thin film transistor of claim 1, wherein the insulation film is formed of a spin-on-glass film.
- 6. (Currently Amended) The thin film transistor of claim 1, wherein a portion of the active layer corresponding to the gate electrode is a channel region, and a portion thereof corresponding to the insulation insulating film is an offset region.

CLAIMS 7-14 (CANCELLED)